1. General description

Logic level N-channel MOSFET in LFPAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

2. Features and benefits

- Enhanced forward biased safe operating area for superior linear mode operation
- Very low Rdson for low conduction losses

3. Applications

- Electronic fuse
- Hot swap
- · Load switch
- · Soft start

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	30	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 2</u>	[1]	-	-	100	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	238	W
Tj	junction temperature			-55	-	175	°C
Static chara	acteristics						
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; Fig. 12		-	1.7	2	mΩ
		V_{GS} = 4.5 V; I_D = 25 A; T_j = 25 °C; Fig. 12		-	3	3.5	mΩ
Dynamic ch	naracteristics			'			
Q_{GD}	gate-drain charge	I _D = 25 A; V _{DS} = 15 V; V _{GS} = 4.5 V; Fig. 14; Fig. 15		-	13.8	-	nC
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 15 V; V _{GS} = 10 V; Fig. 14; Fig. 15		-	87	-	nC
Avalanche i	ruggedness						
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	I_D = 100 A; V_{sup} ≤ 30 V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4		-	-	365	mJ



Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Source-drain d	Source-drain diode						
Q _r	recovered charge	I_S = 25 A; dI_S/dt = 100 A/ μ s; V_{GS} = 0 V; V_{DS} = 15 V		-	49.8	-	nC

[1] Capped at 100A due to package

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	
2	S	source		D
3	S	source	a	
4	G	gate		G_(J≦Д)
mb	D	mounting base; connected to drain	LFPAK56; Power- SO8 (SOT669)	mbb076 S

6. Ordering information

Table 3. Ordering information

Type number			
	Name	Description	Version
PSMN2R0-30YLE	LFPAK56; Power-SO8	plastic, single-ended surface-mounted package; 4 terminals	SOT669

7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN2R0-30YLE	2R030

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	30	V
V_{DGR}	drain-gate voltage	25 °C ≤ Tj ≤ 175 °C; RGS = 20 kΩ		-	30	V
V _{GS}	gate-source voltage			-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	238	W
I _D	drain current	V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 2</u>	[1]	-	100	Α
		V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	100	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 \text{ °C}$; Fig. 3		-	1015	Α
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
Source-drain	n diode			<u> </u>		
Is	source current	T _{mb} = 25 °C	[1]	-	100	Α
I _{SM}	peak source current	pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C		-	1015	Α
Avalanche r	uggedness			'	1	
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	I_D = 100 A; $V_{sup} \le 30$ V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4		-	365	mJ

[1] Capped at 100A due to package

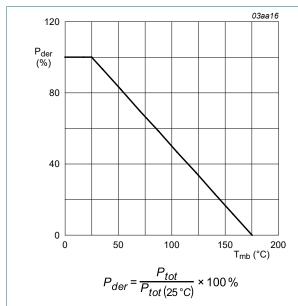


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

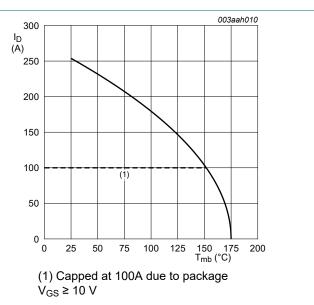


Fig. 2. Continuous drain current as a function of mounting base temperature

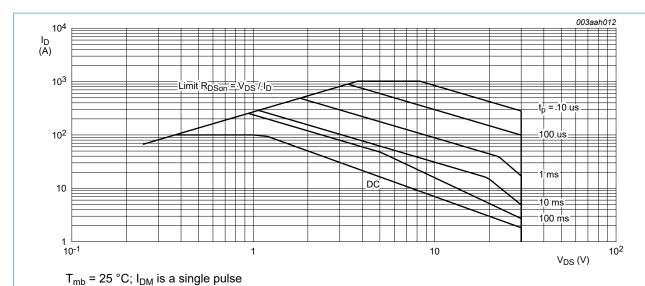
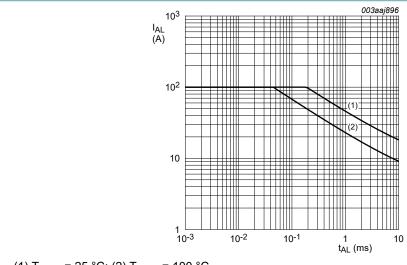


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



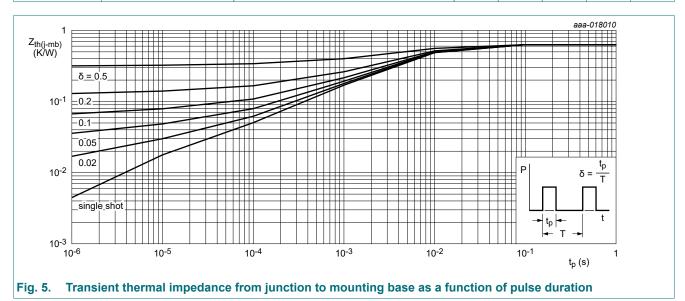
(1) $T_{j \text{ (init)}} = 25 \text{ °C; (2)} T_{j \text{ (init)}} = 100 \text{ °C}$

Fig. 4. Single pulse avalanche rating; avalanche current as a function of avalanche time

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	0.55	0.63	K/W



10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source	I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	27	-	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	30	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 175 °C; Fig. 10	0.5	-	-	V
		I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 25 °C; <u>Fig. 10</u> ; <u>Fig. 11</u>	1.3	1.7	2.15	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}; Fig. 10$	-	-	2.45	V
I _{DSS}	drain leakage current	V _{DS} = 30 V; V _{GS} = 0 V; T _j = 25 °C	-	0.05	10	μA
		V _{DS} = 30 V; V _{GS} = 0 V; T _j = 100 °C	-	-	200	μA
lgss	gate leakage current	V _{GS} = 16 V; V _{DS} = 0 V; T _j = 25 °C	-	10	100	nA
		V _{GS} = -16 V; V _{DS} = 0 V; T _j = 25 °C	-	10	100	nA
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_{D} = 25 A; T_{j} = 25 °C; Fig. 12	-	1.7	2	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 100 °C; Fig. 12; Fig. 13	-	-	2.8	mΩ
		V _{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C; Fig. 12	-	3	3.5	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; Fig. 12; Fig. 13	-	-	3.8	mΩ
R_G	gate resistance	f = 1 MHz	0.3	0.6	1.2	Ω
Dynamic ch	naracteristics		'			
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 15 V; V _{GS} = 10 V; Fig. 14; Fig. 15	-	87	-	nC
		I _D = 25 A; V _{DS} = 15 V; V _{GS} = 4.5 V; Fig. 14; Fig. 15	-	41	-	nC
		I _D = 0 A; V _{DS} = 0 V; V _{GS} = 10 V	-	79	-	nC
Q _{GS}	gate-source charge	I _D = 25 A; V _{DS} = 15 V; V _{GS} = 4.5 V;	-	13.3	-	nC
Q _{GS(th)}	pre-threshold gate- source charge	Fig. 14; Fig. 15	-	8.1	-	nC
Q _{GS(th-pl)}	post-threshold gate- source charge		-	5.2	-	nC
Q_{GD}	gate-drain charge		-	13.8	-	nC
V _{GS(pl)}	gate-source plateau voltage	I _D = 25 A; V _{DS} = 15 V; <u>Fig. 14</u> ; <u>Fig. 15</u>	-	2.8	-	V
C _{iss}	input capacitance	V _{DS} = 15 V; V _{GS} = 0 V; f = 1 MHz;	-	5217	-	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 16</u>	-	1015	-	pF
C _{rss}	reverse transfer capacitance		-	474	-	pF
d(on)	turn-on delay time	V_{DS} = 15 V; R_L = 0.6 Ω ; V_{GS} = 4.5 V;	-	32.7	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega; T_j = 25 °C$	-	55.7	-	ns
t _{d(off)}	turn-off delay time	1	-	41.5	-	ns
t _f	fall time	1	-	29.5	-	ns

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-drain o	liode					
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 17$	-	8.0	1.2	V
t _{rr}	reverse recovery time	$I_S = 25 \text{ A}; dI_S/dt = 100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	42.6	-	ns
Q _r	recovered charge	V _{DS} = 15 V	-	49.8	-	nC

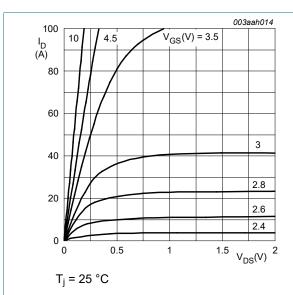


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

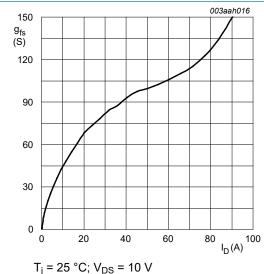


Fig. 8. Forward transconductance as a function of drain current; typical values

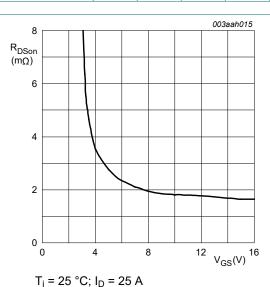


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

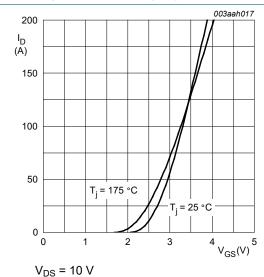


Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

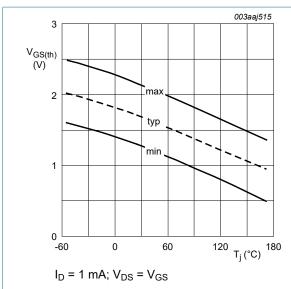


Fig. 10. Gate-source threshold voltage as a function of junction temperature

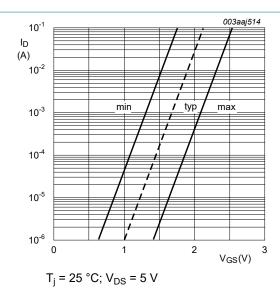


Fig. 11. Sub-threshold drain current as a function of gate-source voltage

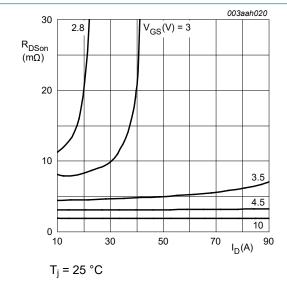


Fig. 12. Drain-source on-state resistance as a function of drain current; typical values

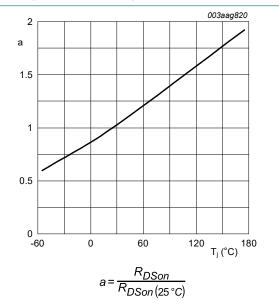


Fig. 13. Normalized drain-source on-state resistance factor as a function of junction temperature

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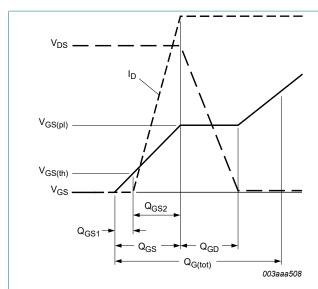


Fig. 14. Gate charge waveform definitions

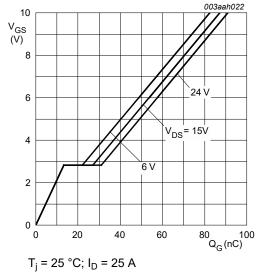


Fig. 15. Gate-source voltage as a function of gate charge; typical values

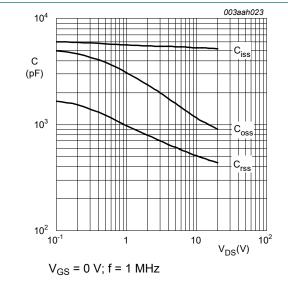
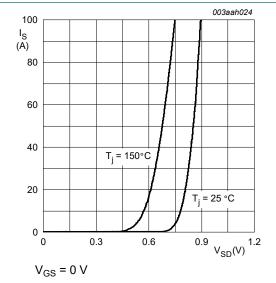


Fig. 16. Input, output and reverse transfer capacitances | Fig. 17. Source current as a function of source-drain as a function of drain-source voltage; typical values



voltage; typical values

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11. Package outline

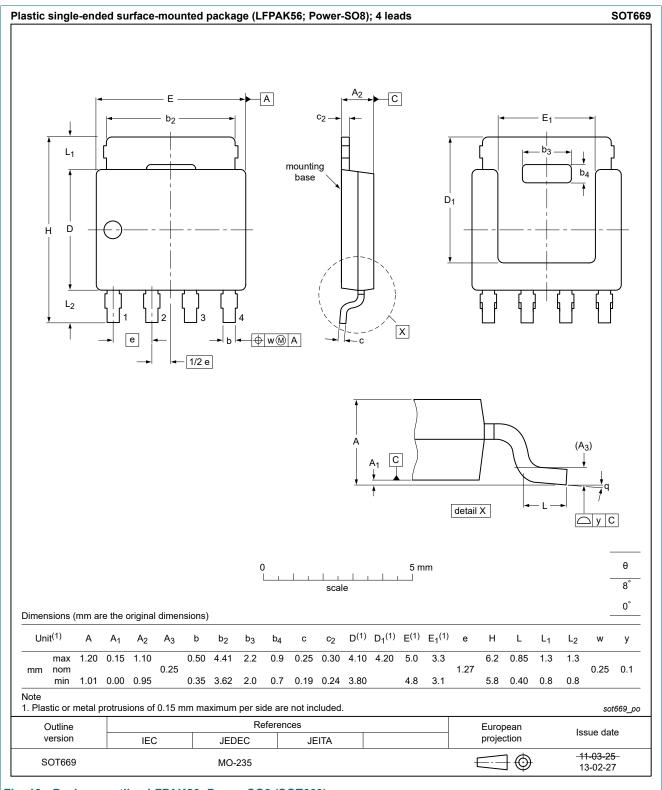
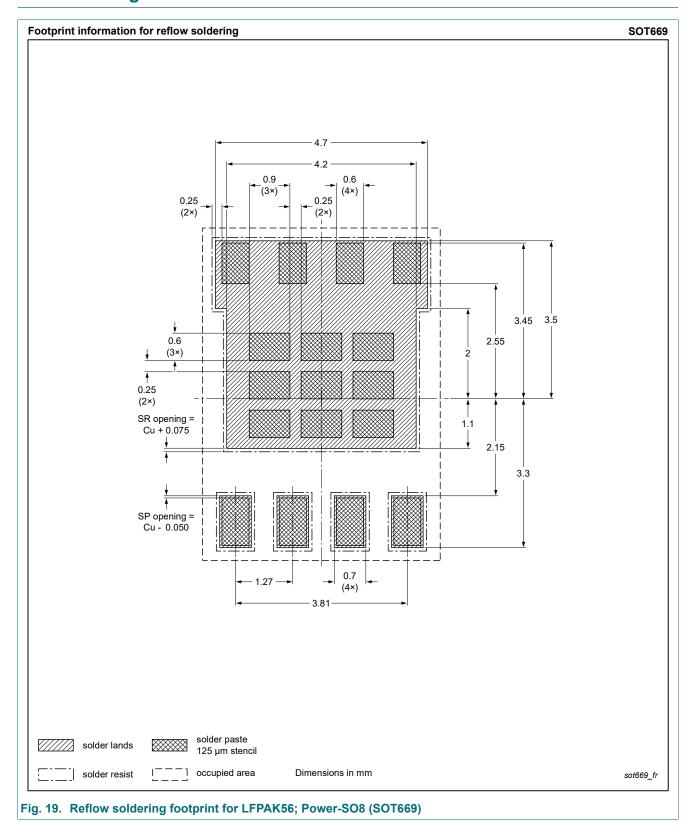
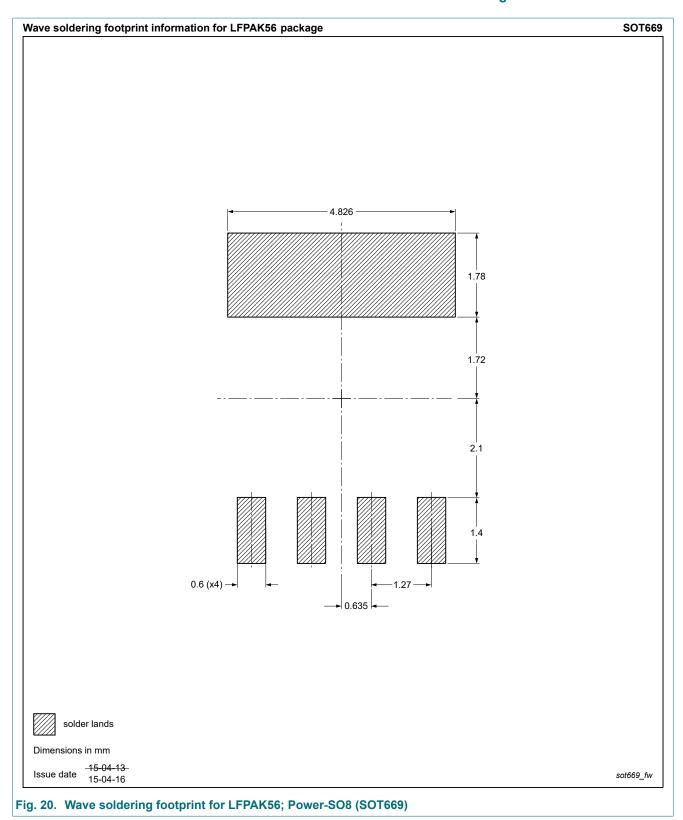


Fig. 18. Package outline LFPAK56; Power-SO8 (SOT669)

12. Soldering



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PSMN2R0-30YLE

13. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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